

# **Technical Note**

## Error Correction Code (ECC) in Micron® Single-Level Cell (SLC) NAND

#### **Introduction**

This technical note describes how to implement error correction code (ECC) in small page and large page Micron<sup>®</sup> single-level cell NAND Flash memory that can detect 2-bit errors and correct 1-bit errors per 256 or 512 bytes.

Refer to the SLC NAND Flash memory data sheets for further information, including the full list of NAND Flash memory devices covered by this technical note. Examples of software ECC are available from your local Micron distributor (see "References" on page 12).

#### Software ECC

When digital data is stored in nonvolatile memory, it is crucial to have a mechanism that can detect and correct a certain number of errors. Error correction code (ECC) encodes data in such a way that a decoder can identify and correct errors in the data.

Typically, data strings are encoded by adding a number of redundant bits to them. When the original data is reconstructed, a decoder examines the encoded message to check for any errors.

There are two basic types of ECC (see Figure 1 on page 2):

- Block codes: These codes are referred to as "n" and "k" codes. A block of k data bits is encoded to become a block of n bits called a code word. In block codes, code words do not have any dependency on previously encoded messages. NAND Flash memory devices typically use block codes.
- Convolution codes: These codes produce code words that depend on both the data message and a given number of previously encoded messages. The encoder changes state with every message processed. Typically, the length of the code word constant.

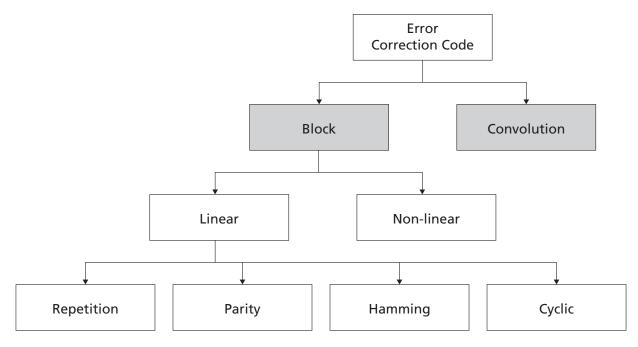
### **Block Codes**

As previously described, block codes are referred to as n and k codes. A block of k data bits is encoded to become a block of n bits called a code word. A block code takes k data bits and computes (n - k) parity bits from the code generator matrix.

The block code family can be divided in linear and non-linear codes, as shown in Figure 1. Either type can be systematic. Most block codes are systematic in that the data bits remain unchanged, with the parity bits attached either to the front or to the back of the data sequence.



Figure 1: Block Codes

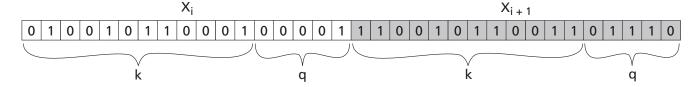


## **Systematic Codes**

In systematic (linear or non-linear) block codes, each code word includes the exact data bits from the original message of length k, either followed or preceded by a separate group of check bits of length q (see Figure 2). The ratio k / (k + q) is called the code rate. Improving the quality of a code often means increasing its redundancy and, thus, reducing the code rate.

The set of all possible code words is called the code space.

Figure 2: Systematic Codes



#### **Linear Codes**

In linear block codes, every linear combination of valid code words (such as a binary sum) produces another valid code word. In all linear codes, the code words are longer than the data words on which they are based.

Micron NAND Flash memory devices use cyclic and Hamming linear codes.

#### **Cyclic Codes**

Cyclic codes are a type of linear code where every cyclic shift by a valid code word also yields a valid code word.

# TN-29-63 Error Correction Code (ECC) in SLC NAND Systematic Codes

#### **Hamming Codes**

Hamming codes are the most widely used linear block codes. Typically, a Hamming code is defined as (2n - 1, 2n - n - 1), where:

- n is equal to the number of overhead bits.
- 2n 1 is equal to the block size.
- 2n n 1 is equal to the number of data bits in the block.

All Hamming codes can detect three errors and one correct one. Common Hamming code sizes are (7, 4), (15,11), and (31, 26). All have the same Hamming distance.

The Hamming distance and the Hamming weight are useful in encoding. When the Hamming distance is known, the capability of a code to detect and correct errors can be determined.

#### **Hamming Distance**

In continuous variables, distances are measured using euclidean concepts, such as lengths, angles, and vectors.

In binary encoding, the distance between two binary words is called the Hamming distance. It is the number of discrepancies between two binary sequences of the same size. The Hamming distance measures how different the binary objects are. For example, the Hamming distance between sequences 0011001 and 1010100 is 4.

The Hamming code minimum distance  $d_{min}$  is the minimum distance between all code word pairs.

### **Hamming Weight**

The Hamming weight of a code scheme is the maximum number of 1s among valid code words.

#### **Error Detection Capability**

For a code where  $d_{min}$  is the Hamming distance between code words, the maximum number of error bits that can be detected is  $t = d_{min}$  - 1. This means that 1-bit and 2-bit errors can be detected for a code where  $d_{min}$  = 3.

#### **Error Correction Capability**

For a code where  $d_{min}$  is the Hamming distance between code words, the maximum number of error bits that can be corrected is  $t = (d_{min} - 1) \S 2$ . This means that 1-bit errors can be corrected for a code where  $d_{min} = 3$ .

### TN-29-63 Error Correction Code (ECC) in SLC NAND **ECC for Memory Devices**

## **ECC for Memory Devices**

Common error correction capabilities for memory devices are:

- Single error correction (SEC) Hamming codes
- Single error correction/double error detection (SEC-DED) Hsiao codes
- Single error correction/double error detection/single byte error detection (SEC-DED-SBD) Reddy codes
- Single byte error correction/double byte error detection (SBC-DBD) finite field-based codes
- Double error correction/triple error detection (DEC-TED) Bose-Chaudhuri-Hocquenghem codes

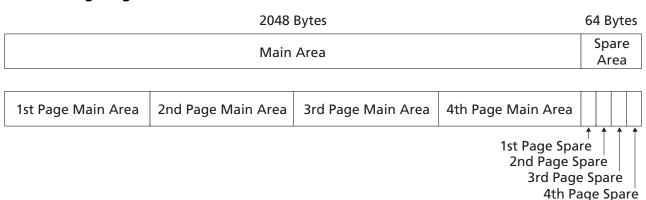
### **ECC Generation**

According to the Hamming ECC principle, a 22-bit ECC is generated to perform a 1-bit correction per 256 bytes. The Hamming ECC can be applied to data sizes of 1 byte, 8 bytes, 16 bytes, and so on.

For 528-byte/264-word page NAND devices, a Hamming ECC principle can be used that generates a 24-bit ECC per 512 bytes to perform a 2-bit detection and a 1-bit correction.

For 2112-byte/1056-word page NAND devices, the calculation can be done per 512 bytes, which means a 24-bit ECC per 4096 bits (exactly 3 bytes per 512 bytes). 2112 byte pages are divided into 512 byte (+ 16 byte spare) chunks (see Figure 3).

Figure 3: **Large Page Divided Into Chunks** 



The 24 ECC bits are arranged in three bytes (see Table 1).

Table 1: **Assignment of Data Bits With ECC Code** 

ECC	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Ecc0 <sup>1</sup>	LP07	LP06	LP05	LP04	LP03	LP02	LP01	LP00
Ecc1 <sup>2</sup>	LP15	LP14	LP13	LP12	LP11	LP10	LP09	LP08
Ecc2 <sup>3</sup>	CP5	CP4	CP3	CP2	CP1	CP0	LP17	LP16

- **Notes:** 1. The first byte (Ecc0) contains line parity bits LP0–LP07.
  - 2. The second byte (Ecc1) contains line parity bits LP08–LP15.
  - 3. The third byte (Ecc2) contains column parity bits CP0-CP5, plus LP16 and LP17 generated only for a 512-byte input.

# TN-29-63 Error Correction Code (ECC) in SLC NAND ECC for Memory Devices

For every data byte in each page, 16 or 18 bits for line parity and 6 bits for column parity are generated according to the scheme shown in Figure 4.

Figure 4: Parity Generation

Byte 0	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	LPO	LPO2		
Byte 1	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	LP1	LPUZ		LP14 <sup>2</sup>
Byte 2	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	LPO	LPO3		LF 14
Byte 3	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	LP1	LPUS		
Byte 252	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	LPO	LPO2		
Byte 253	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	LP1	LFUZ		LP15 <sup>2</sup>
Byte 254	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	LPO	LPO3	•••	LF13
Byte 255 <sup>1</sup>	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	LP1	LFO3		
CP1         CP0         CP1         CP0         CP1         CP0           CP3         CP2         CP3         CP2												
	CP5					CI	P4					

**Notes:** 1. For 512-byte inputs, the highest byte number is 511.

**2.** For 512-byte inputs, additional XOR operations must be executed. Also, the last line parity bits calculated are LP16 and LP17 instead of LP14 and LP15, respectively. The column parity bits are unchanged.



#### **ECC Generation Pseudo Code**

```
The following pseudo code implements the parity generation shown in Figure 4 on
page 5.
For i = 1 \text{ to } 256^1
begin
    if (i & 0x01)
     LP1=bit7 \oplus^1 bit6 \oplus bit5 \oplus bit4 \oplus bit3 \oplus bit2 \oplus bit1 \oplus bit0 \oplus LP1; 
else
    LP0=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0
⊕ LP1;
if (i & 0x02)
    LP3=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0
⊕ LP3;
else
    LP2=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0
⊕ LP2;
if (i & 0x04)
    LP5=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0
⊕ LP5;
else
    LP4=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0
⊕ LP4;
if (i & 0x08)
    LP7=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0
⊕ LP7;
else
    LP6=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0
⊕ LP6;
if (i & 0x10)
    LP9=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0
⊕ LP9;
else
    LP8=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0
⊕ LP8;
if (i & 0x20)
    LP11=bit7 \oplus bit6 \oplus bit5 \oplus bit4 \oplus bit3 \oplus bit2 \oplus bit1 \oplus bit0 \oplus LP11;
else
LP10=bit7 ⊕ bit6 ⊕ bit5 ⊕ bit4 ⊕ bit3 ⊕ bit2 ⊕ bit1 ⊕ bit0 ⊕
LP10:
if (i & 0x40)
```

LP13=bit7  $\oplus$  bit6  $\oplus$  bit5  $\oplus$  bit4  $\oplus$  bit3  $\oplus$  bit2  $\oplus$  bit1  $\oplus$  bit0  $\oplus$  LP13;

### TN-29-63 Error Correction Code (ECC) in SLC NAND **ECC for Memory Devices**

```
else
     LP12=bit7 \oplus bit6 \oplus bit5 \oplus bit4 \oplus bit3 \oplus bit2 \oplus bit1 \oplus bit0
⊕ LP12; if (i & 0x80)
     LP15=bit7 \oplus bit6 \oplus bit5 \oplus bit4 \oplus bit3 \oplus bit2 \oplus bit1 \oplus bit0 \oplus LP15;
else
     LP14=bit7 \oplus bit6 \oplus bit5 \oplus bit4 \oplus bit3 \oplus bit2 \oplus bit1 \oplus bit0 \oplus LP14;
if(i & A0)
     LP17=bit7 (Xor) bit6 (Xor) bit5 (Xor) bit4 (Xor) bit3 (Xor) bit2
(Xor) bit1 (Xor) bit0 (Xor) LP17
else
     LP16=bit7 (Xor) bit6 (Xor) bit5 (Xor) bit4 (Xor) bit3 (Xor) bit2
(Xor) bit1 (Xor) bit0 (Xor) LP16<sup>3</sup>
CP0 = bit6 \oplus bit4 \oplus bit2 \oplus bit0 \oplus CP0;
CP1 = bit7 \oplus bit5 \oplus bit3 \oplus bit1 \oplus CP1;
CP2 = bit5 \oplus bit4 \oplus bit1 \oplus bit0 \oplus CP2;
CP3 = bit7 \oplus bit6 \oplus bit3 \oplus bit2 \oplus CP3
CP4 = bit3 \oplus bit2 \oplus bit1 \oplus bit0 \oplus CP4
CP5 = bit7 \oplus bit6 \oplus bit5 \oplus bit4 \oplus CP5
end
```

- **Notes:** 1. For 512-byte inputs, the "i" range is from 1–512 bytes.
  - 2. "⊕" indicates a bitwise XOR operation.
  - **3.** The last control "if(i & A0)" is executed only in the case of 512-byte inputs.

#### **ECC Detection and Correction**

ECC can detect the following:

- **No error**: The result of XOR is 0.
- Correctable error: The result of XOR is a code with 11 bits at 1. For 512-byte inputs, the generated ECC has 12 bits at 1.
- ECC error: The result of XOR has only 1 bit at 1. This means that the error is in the ECC
- Non-correctable error: The result of XOR provides all other results.

When the main area has a 1-bit error, each parity pair (for example, LP0 and LP1) is 1 and 0 or 0 and 1.

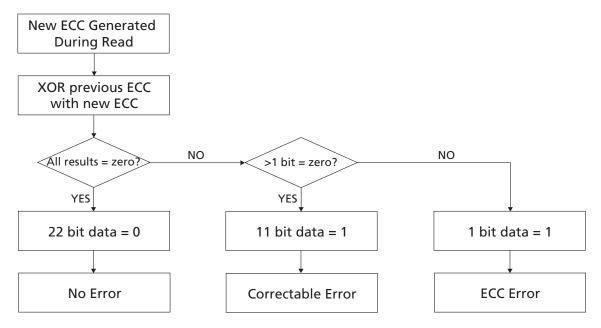
The fail bit address offset can be obtained by retrieving the following bits from the result of XOR:

- Byte address = (LP17,LP15,LP13,LP11,LP9,LP7,LP5,LP3,LP1). For 512-byte inputs, the resulting byte address is LP17.
- Bit address = (CP5, CP3, CP1)

When the NAND devices has more than two bit errors, the data cannot be corrected.



Figure 5: ECC Detection



**Notes:** 1. For 512-byte inputs, the generated ECC is has 12 bits at 1.

2. For 512-byte inputs, the generated ECC is 24 bits long.

#### **ECC Detection and Correction Pseudo Code**

```
% Detect and correct a 1 bit error for 256 byte block
int ecc check (data, stored ecc, new ecc)
begin
% Basic Error Detection phase
ecc xor[1] = new ecc[1] 
   stored ecc[1];
if ((ecc xor[0] or ecc xor[1] or ecc xor[2]) == 0)
   begin
   return 0; % No errors
end
else
   begin
      % Counts the bit number
      bit count = BitCount(ecc xor);
          if (bit count == 11)
      begin
      % Set the bit address
      bit address = (ecc xor[2] >> 3) and 0x01 or
```

# TN-29-63 Error Correction Code (ECC) in SLC NAND ECC for Memory Devices

```
(ecc xor[2] \gg 4) and 0x02 or
        (ecc xor[2] \gg 5) and 0x04;
    byte address = (ecc xor[0] >> 1) and 0x01 or
        (ecc xor[0] >> 2) and 0x02 or
        (ecc xor[0] >> 3) and 0x04 or
        (ecc xor[0] >> 4) and 0x08 or
        (ecc xor[1] \ll 3) and 0x10 or
        (ecc xor[1] \ll 2) and 0x20 or
        (ecc\_xor[1] << 1) and 0x40 or
        (ecc xor[1] and 0x80);
    % Correct bit error in the data
    data[byte address] = data[byte address] (0x01<<bit address);</pre>
    return 1;
    end
    else if (bit count == 1)
    begin
        % ECC Code Error Correction
        stored ecc[0] = new ecc[0];
        stored ecc[1] = new ecc[1];
        stored ecc[2] = new ecc[2];
    return 2;
    end
    else
    begin
        % Uncorrectable Error
        return -1;
        end
end
end
```

Note:

"⊕" indicates bitwise XOR.

## TN-29-63 Error Correction Code (ECC) in SLC NAND ECC Software Interface

## **ECC Software Interface**

Micron supplies a software implementation of the algorithm in the c1823.zip file (see "References" on page 12). The software interface implementation consists of two public functions:

```
void make_ecc(ubyte *ecc_code,const ubyte *data);
that calculates the 3-byte ECC, and
eccdiff_t ecc_check(ubyte *data, ubyte *stored_ecc, ubyte
*new_ecc);
that detects and corrects a 1-bit error.
```

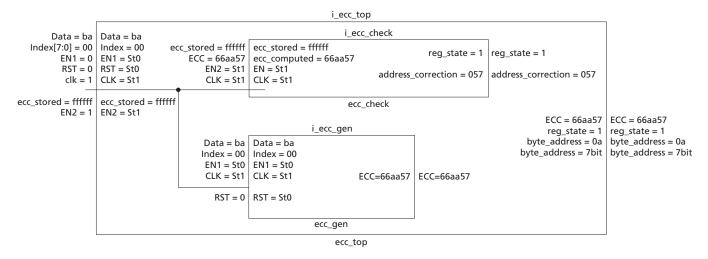
#### Where:

- Stored\_ecc is the ECC stored in the NAND Flash memory.
- *New\_ecc* is the ECC code generated on the data page read operation.

## **ECC Hardware Code Generation and Correction - Verilog Model**

The hardware code generation and correction schematics are shown in Figure 6. The function details are provided in Table 2 on page 11. The interface for the hardware model is: module ecc\_top(Data, Index, ECC, EN1, RST, ecc\_stored, reg\_state, byte\_address, bit address, EN2, CLK).

Figure 6: Hardware Code Generation and Correction



**Table 2: Module Ecc\_top Hardware Interface** 

Interface Type		Description				
Data	input [7:0]	A single byte.				
Index input [7:0]		The current data position in the page (0-255).				
ECC output [23:0]		Three bytes of ECC.				
EN1 input		Enable for the ecc_gen module.				
RST input		Reset.				
ecc_stored	input [23:0]	The ECC value stored in the NAND Flash memory.				
reg_state	output [2:0]	A register that shows the state of the ecc_check module.	define No_Error 000			
			define Correctable_Error 001			
			define Ecc_Error 010			
			define Non_Correctable_Error 100			
byte_address output [7:0]		Byte address of the defective data bit.				
bit_address output [2:0		Bit address of the defective data bit.				
EN2 input		Enable for the ecc_check module.				
CLK input		Clock.				



## TN-29-63 Error Correction Code (ECC) in SLC NAND Conclusion

## **Conclusion**

The implementation of ECC in devices used for data storage is recommended. Hamming-based block codes are commonly used ECC for NAND Flash memory devices. By using a Hamming ECC in Micron NAND Flash memory devices, 2-bit errors can be detected and 1-bit errors corrected. This minimizes possible errors and helps to extend the lifetime of the memory device.

### References

- NANDxxx-A single-level cell small page NAND Flash memory family data sheets
- NANDxxx-B single-level cell large page NAND Flash memory family data sheets
- Examples of software ECC, which are available from your local distributor

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